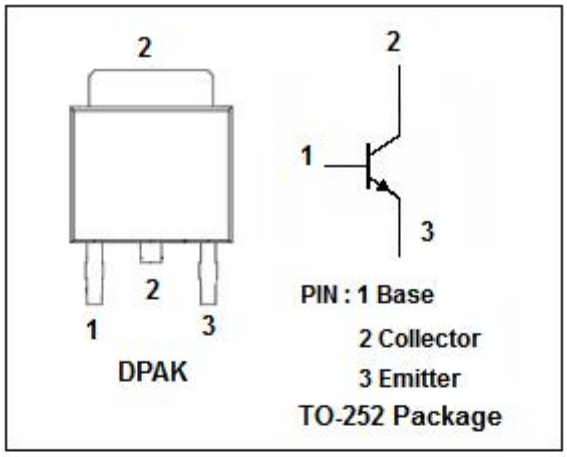
isc Silicon NPN Power Transistor 2SCR572D

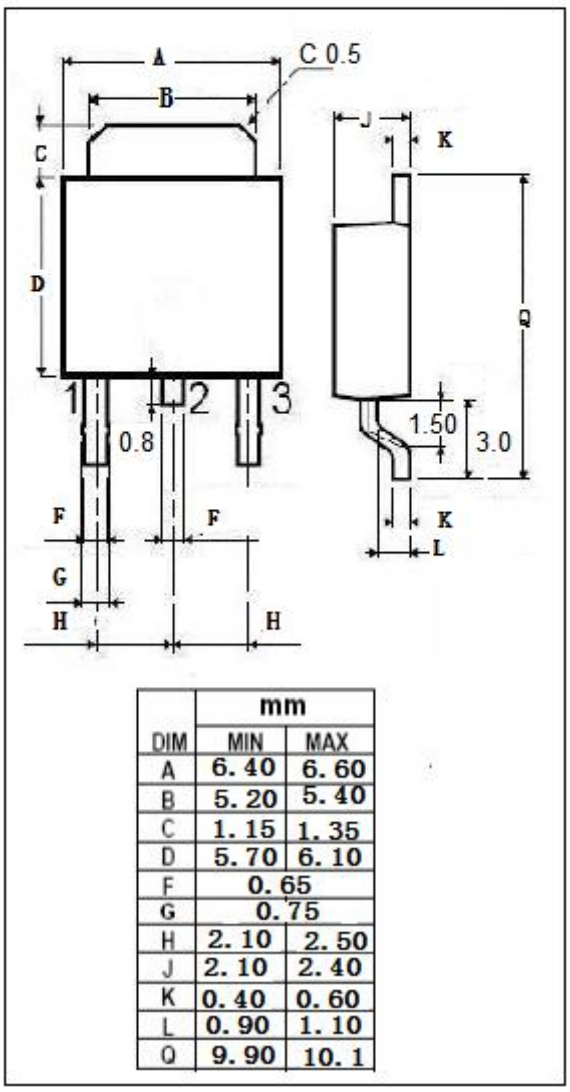


DESCRIPTION

- Suitable for middle power drivers
- Low $V_{CE(sat)}$
  $V_{CE(sat)}$=0.4V@(I_C=2A,I_B=0.1A)
- Complementary NPN types:2SAR572D
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Low frequency amplifier



DIM	mm MIN	MAX
A	6.40	6.60
B	5.20	5.40
C	1.15	1.35
D	5.70	6.10
F	0.65	
G	0.75	
H	2.10	2.50
J	2.10	2.40
K	0.40	0.60
L	0.90	1.10
Q	9.90	10.1

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	30	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	5	A
I_{CM}	Collector Current-Peak	10	A
P_C	Collector Power Dissipation @ T_C=25℃	10	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
BV_{CBO}	Collector-Base breakdown voltage	I_C=100uA	30			V
BV_{CEO}	Collector-Emitter breakdown voltage	I_C=1mA	30			V
BV_{EBO}	Emitter-Base breakdown voltage	I_E=100uA	6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 2A; I_B= 100mA			0.4	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 30V; I_E= 0			1.0	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 4V; I_C= 0			1.0	μA
h_{FE}	DC Current Gain	I_C= 0.5A; V_{CE}= 3V	200		500	
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= 10V; f= 1.0MHz		30		pF
f_T[NOTE]	Current-Gain—Bandwidth Product	I_C= 0.5A; V_{CE}= 10V,f= 100MHz		300		MHz

NOTE:Pulsed